

Part Number: KB-2785YW

Yellow

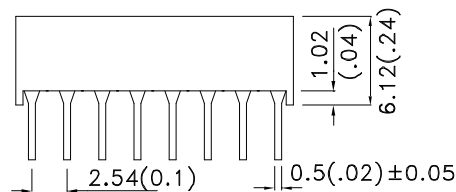
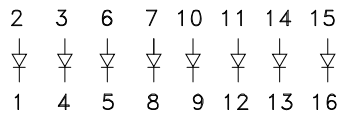
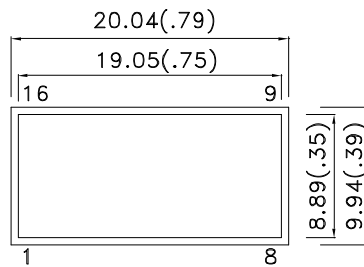
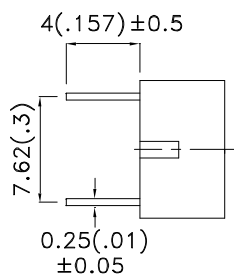
### Features

- UNIFORM LIGHT EMITTING AREA.
- LOW CURRENT OPERATION.
- EASILY MOUNTED ON P.C. BOARDS.
- FLUSH MOUNTABLE.
- EXCELLENT ON/OFF CONTRAST.
- CAN BE USED WITH PANELS AND LEGEND MOUNTS.
- RoHS COMPLIANT.

### Description

The Yellow source color devices are made with Gallium Arsenide Phosphide on Gallium Phosphide Yellow Light Emitting Diode.

### Package Dimensions & Internal Circuit Diagram



Notes:

1. All dimensions are in millimeters (inches), Tolerance is ±0.25(0.01") unless otherwise noted.
2. Specifications are subject to change without notice.



## Selection Guide

Part No.	Dice	Lens Type	Iv (mcd) [1] @ 20mA	
			Min.	Typ.
KB-2785YW	Yellow (GaAsP/GaP)	WHITE DIFFUSED	10	50

Note:

1. Luminous intensity/ luminous Flux: +/-15%.

## Electrical / Optical Characteristics at TA=25°C

Symbol	Parameter	Device	Typ.	Max.	Units	Test Conditions
$\lambda_{peak}$	Peak Wavelength	Yellow	590		nm	I <sub>F</sub> =20mA
$\lambda_D$ [1]	Dominant Wavelength	Yellow	588		nm	I <sub>F</sub> =20mA
$\Delta\lambda_{1/2}$	Spectral Line Half-width	Yellow	35		nm	I <sub>F</sub> =20mA
C	Capacitance	Yellow	20		pF	V <sub>F</sub> =0V;f=1MHz
V <sub>F</sub> [2]	Forward Voltage (per chip)	Yellow	2.1	2.5	V	I <sub>F</sub> =20mA
I <sub>R</sub>	Reverse Current (per chip)	Yellow		10	uA	V <sub>R</sub> =5V

Notes:

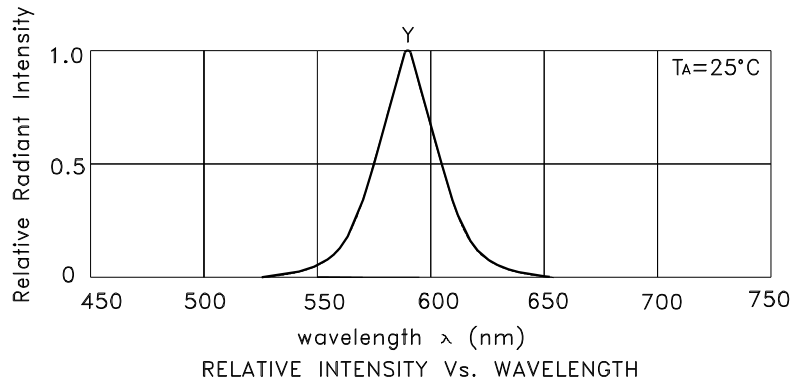
- 1.Wavelength: +/-1nm.
2. Forward Voltage: +/-0.1V.

## Absolute Maximum Ratings at TA=25°C

Parameter	Yellow	Units
Power dissipation (per chip)	75	mW
DC Forward Current (per chip)	30	mA
Peak Forward Current [1] (per chip)	140	mA
Reverse Voltage (per chip)	5	V
Operating / Storage Temperature	-40°C To +85°C	
Lead Solder Temperature[2]	260°C For 3-5 Seconds	

Notes:

1. 1/10 Duty Cycle, 0.1ms Pulse Width.
2. 2mm below package base.



Yellow

KB-2785YW

